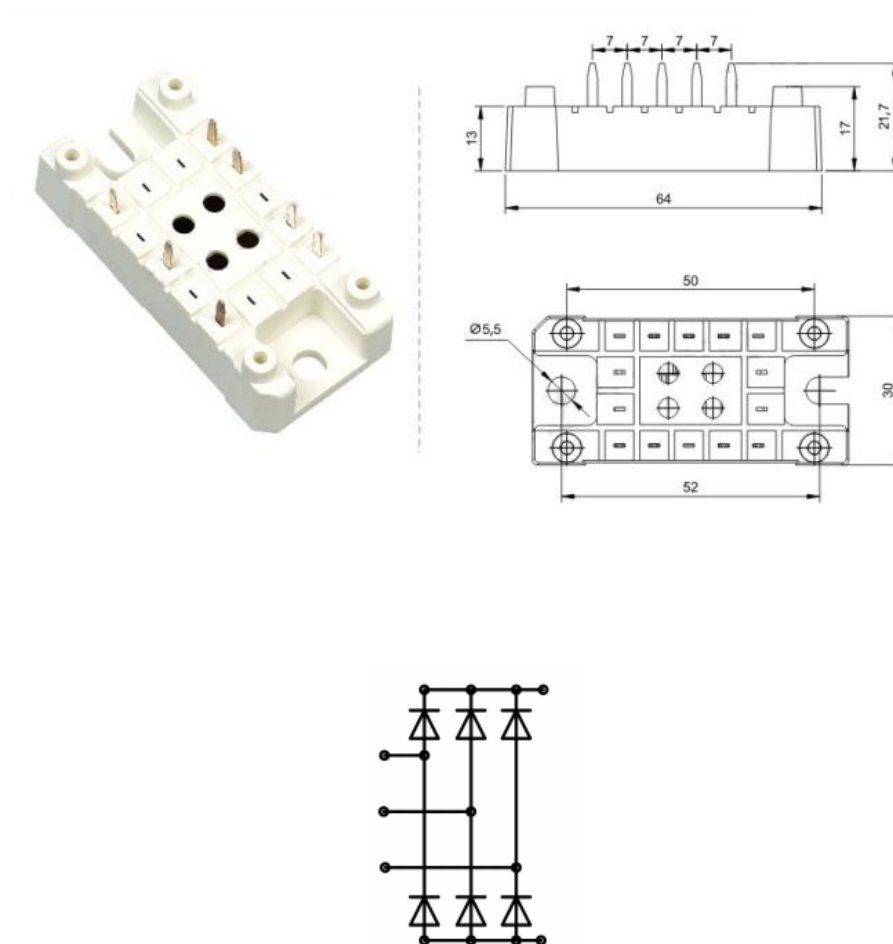


Parameter	Symbol	Conditions	Values	Units
Repetitive Peak Off-State Voltage	V_{DRM}		-	V
Non Repetitive Peak Off-State Voltage	V_{DSM}		-	
Repetitive Peak Reverse Voltage	V_{RRM}		1600	V
Non Repetitive Peak Reverse Voltage	V_{RSM}		1700	V
Average Rectified Output Current	$I_{O(AV)}$	$T_C=100^{\circ}C$	53	A
Surge Forward Current	I_{FSM}	50Hz; Half Sine Wave,1Pulse, Non-Repetitive $T_j=150^{\circ}C$	270	A
I Squared t	I^2t	2msec to 10msec $T_j=150^{\circ}C$	0.365	KA ² s
Surge On-State Current	I_{TSM}	50Hz; Half Sine Wave,1Pulse, Non-Repetitive	-	A
I Squared t	I^2t	2msec to 10msec	-	KA ² s
Peak Forward Voltage	V_{FM}	$T_j=25^{\circ}C$; $I_F=50A$	1.50	V
Peak On-State Voltage	V_{TM}		-	
Threshold voltage	$V_{F(TO)}$	$T_j=150^{\circ}C$	0.8	V
Forward slope resistance	r_F	$T_j=150^{\circ}C$	13	m Ω
Peak Reverse Current	I_{RM}	$V_{RM}=V_{RRM}$, $T_j=125^{\circ}C$	-	mA
Critical Rate of Turned-On Current	di/dt	$V_D=2/3V_{DRM}$, $I_{TM}=2 \cdot I_O$, $T_j=125^{\circ}C$ $I_G=200mA$, di _G /dt=0.2A/ μ s	-	A/ μ s
Critical Rate of Rise of Off-State Voltage	dv/dt	$V_D=2/3V_{DRM}$ $T_j=125^{\circ}C$	-	V/ μ s
Gate Current to Trigger	I_{GT}	$V_D=6V$, $I_T=1A$, $T_j=25^{\circ}C$	-	mA
Gate Voltage to Trigger	V_{GT}		-	V
Holding Current	I_H		-	mA
Thermal Resistance	$R_{th(j-c)}$	Junction to Case	1.9	K/W
	$R_{th(c-f)}$	Case to Fin	2.92	K/W
	T_{vj}		-40~+150	$^{\circ}C$
	T_{stg}		-40~+125	$^{\circ}C$
	V_{isol}	a.c. 50Hz; r.m.s.; 1min./1S	3000/3600	V
Mounting torque	M	Case mounting Terminals	2	N.m

OUTLINE DRAWING (Dimensions in mm)



SKD